THERMAL DATA

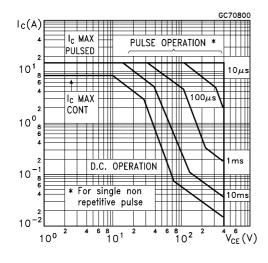
R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W	
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	°C/W	

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

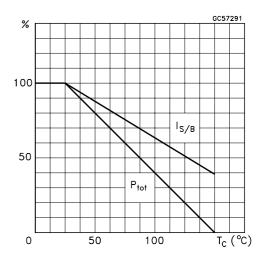
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 700 V V _{CE} = 700 V T _c = 100 °C			10 0.5	μA mA
ICEO	Collector Cut-off Current (I _B = 0)	V _{CE} = 400 V			100	μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 9 V			100	μΑ
$V_{\text{CEO(sus)}^{*}}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 10 mA	400			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$\begin{split} I_C &= 2 \ A & I_B &= 0.4 \ A \\ I_C &= 5 \ A & I_B &= 1 \ A \\ I_C &= 8 \ A & I_B &= 2 \ A \\ I_C &= 5 \ A & I_B &= 1 \ A & T_c &= 100 \ ^{o}C \end{split}$			0.8 1.5 2 3	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage				1.2 1.6 1.5	V V V
h _{FE} *	DC Current Gain	I _C = 2 A	18 8		40 25	
V_{f}	Diode Forward Voltage	I _C = 3 A			2.5	V
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$\begin{array}{lll} I_{C} = 5 \; A & V_{CL} = 250 \; V \; R_{BB} = 0 \Omega \\ I_{B1} = 1 \; A & V_{BE(off)} = -5 \; V \\ L = 200 \; \mu H & (see figure 1) \end{array}$		1.7 90	2.3 150	μs ns
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 5 \text{ A}$ $V_{CL} = 250 \text{ V}$ $R_{BB} = 0\Omega$ $I_{B1} = 1 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $L = 200 \ \mu\text{H}$ $T_{C} = 125 \ ^{\circ}\text{C}$ (see figure 1)		2.2 150		μs ns

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 2 %.

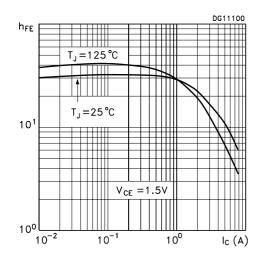
Safe Operating Area



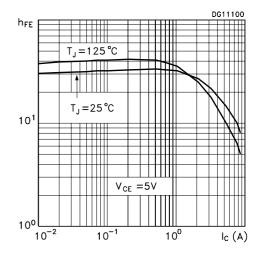
Derating Curve



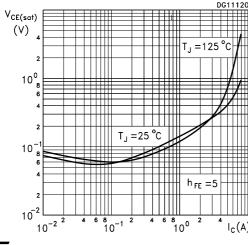
DC Current Gain



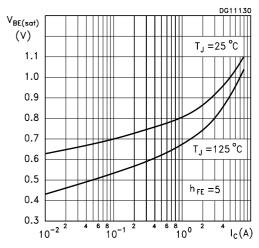
DC Current Gain



Collector Emitter Saturation Voltage

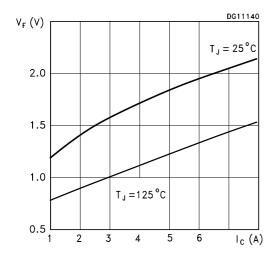


Base Emitter Saturation Voltage

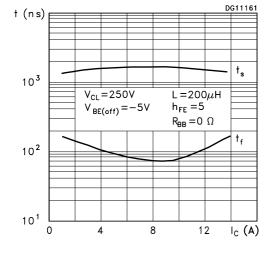


47/

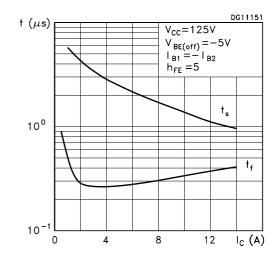
Diode Forward Voltage



Switching Time Inductive Load



Switching Time Resistive Load



Reverse Biased SOA

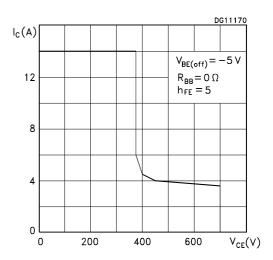


Figure 1: Inductive Load Switching Test Circuit.

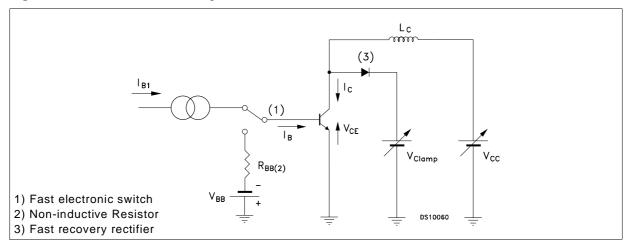
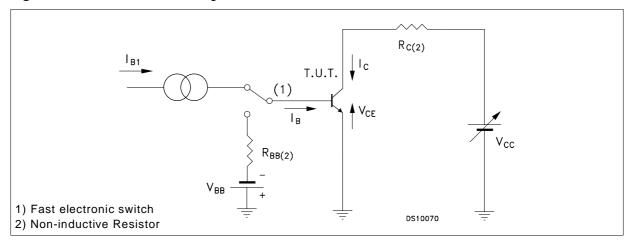
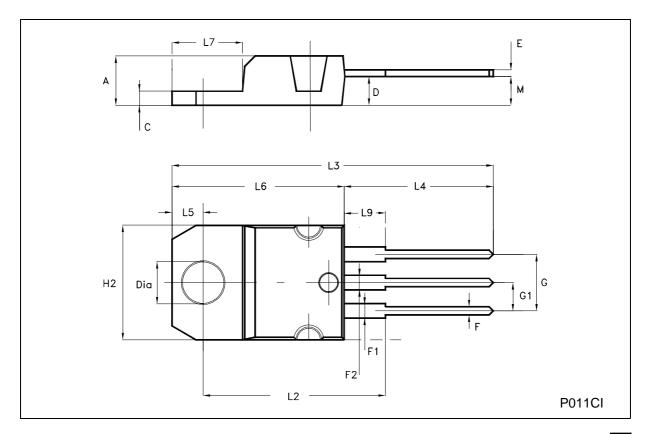


Figure 2: Resistive Load Switching Test Circuit.



TO-220 MECHANICAL DATA

DIM	mm		inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



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47/